

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

Claims 1-41. (Cancelled).

42. (New). A read out method of a semiconductor memory device comprising:
latching data on a data bus into a page latch; and
transferring the data latched in the page latch to a cell matrix for programming the data at a first mode, and to a read out circuit for reading out the data without programming the data latched in the data latch into the cell matrix at a second mode.

43. (New). The read out method of the semiconductor memory device according to the claim 42, wherein the second mode comprises:

a test mode to test whether or not an error occurs at a data transfer circuit group including the data bus, the page latch, and the read out circuit.

44. (New). The read out method of the semiconductor memory device according to the claim 42, wherein the second mode comprises:

a test mode for confirming whether or not an error occurs.

45. (New). The read out method of the semiconductor memory device according to the claim 42, further comprising:

correcting error of data read from the read out circuit.

46. (New). A read out method of a semiconductor memory device comprising:

latching data on a data bus and an inspection data generated by an inspection bits generating circuit into a page latch; and

transferring the data and the inspection data latched in the page latch to a cell matrix at a first mode for programming the data and the inspection data, and to a read out circuit for reading out the data without programming the data and the inspection data into the cell matrix at a second mode.

47. (New). The read out method of the semiconductor memory device according to the claim 46, wherein the second mode comprises:

a test mode to test whether or not an error occurs at a data transfer circuit group including the data bus, the page latch, and the read out circuit.

48. (New). The read out method of the semiconductor memory device according to the claim 46, wherein the second mode comprises:

a test mode for confirming whether or not an error occurs.

49. (New). The read out method of the semiconductor memory device according to the claim 46, further comprising:

correcting error of data read from the read out circuit.